

Features

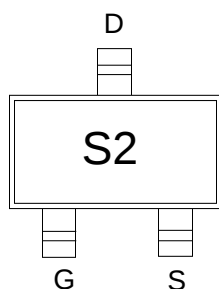
- Trench Power LV MOSFET technology
- High Power and current handing capability

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
20V	55mΩ@4.5V	2A
	75mΩ@2.5V	

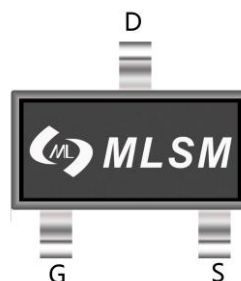
Application

- PWM application
- Load switch

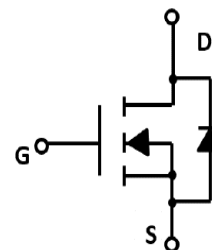


S2: Device code

Marking and pin assignment



SOT-523 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		20	V
V _{GS}	Gate-Source Voltage		±10	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	2.3	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$	9	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$	2.3	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$	0.35	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient		833	°C/W

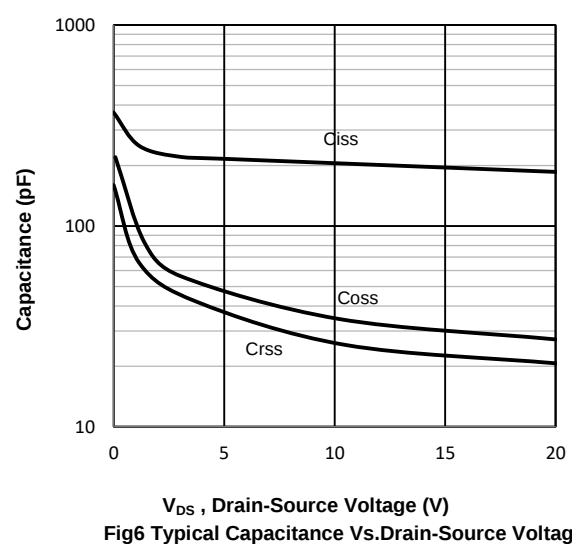
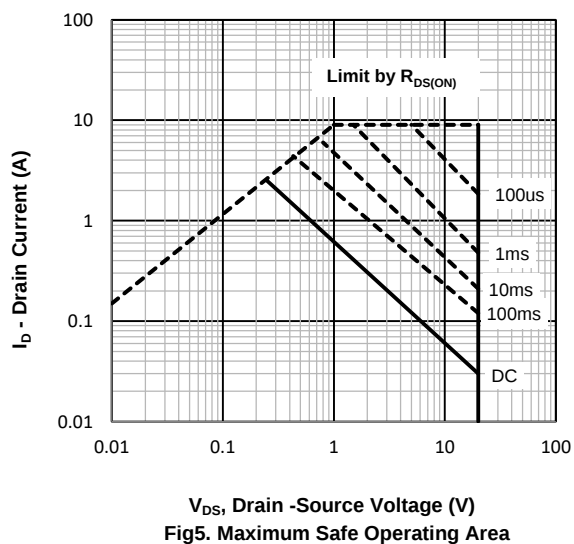
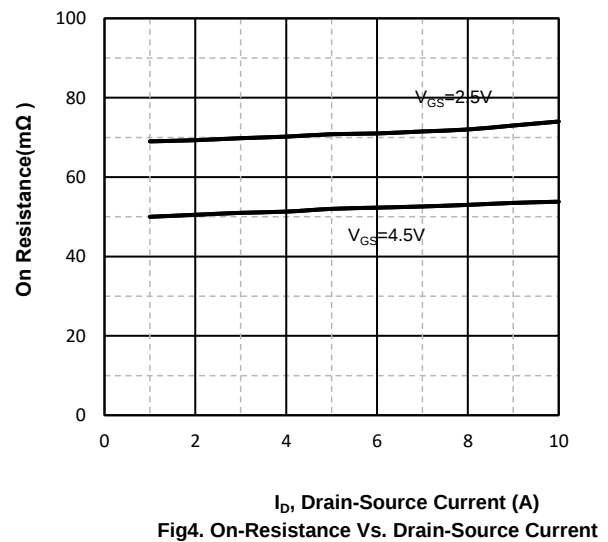
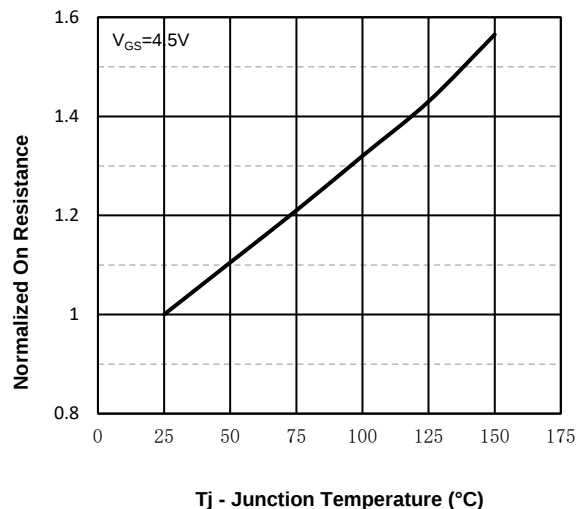
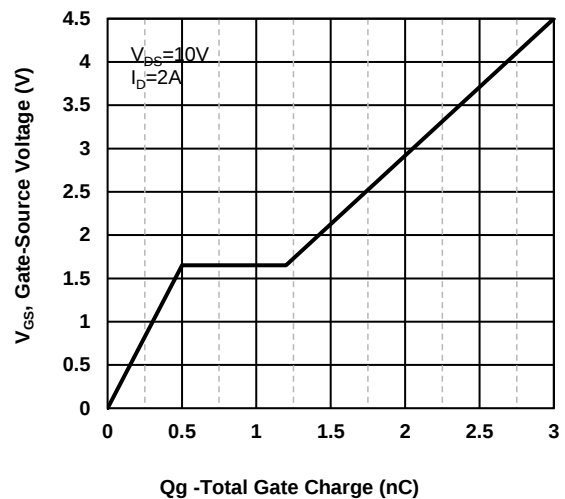
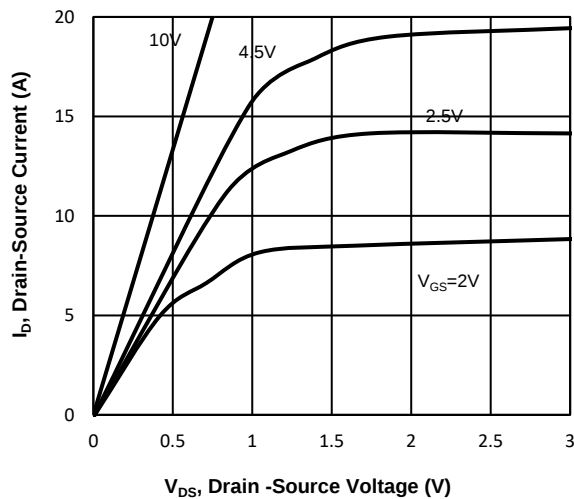
Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS2302T	SOT-523	S2	3,000	45,000	180,000	7" reel

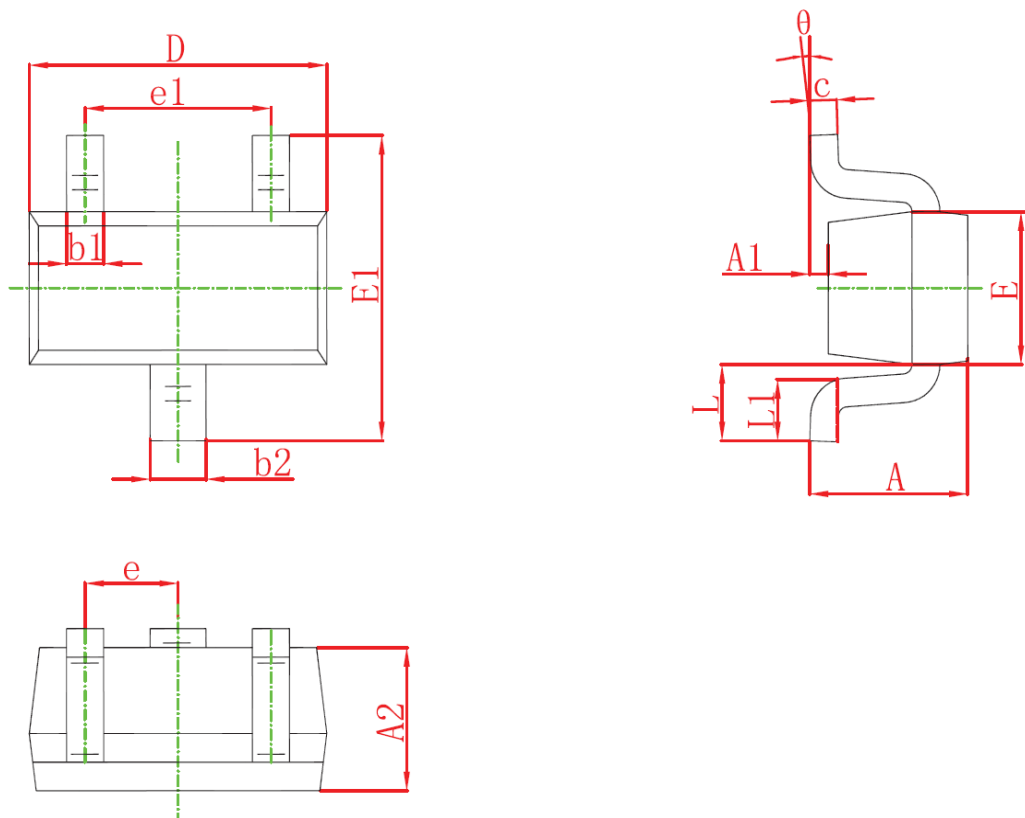
Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	20	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=20V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±10V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	0.45	0.7	0.9	V
RDS(on)	Drain-Source On-State Resistance	VGS=4.5V, ID=2.3A	--	55	100	mΩ
		VGS=2.5V, ID=1.5A	--	75	150	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=10V, VGS=0V, f=1MHz	--	200	--	pF
COSS	Output Capacitance		--	35	--	pF
CRSS	Reverse Transfer Capacitance		--	28	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=10V, ID=2A, VGS=4.5V	--	3	--	nC
Qgs	Gate Source Charge		--	0.5	--	nC
Qgd	Gate Drain Charge		--	0.7	--	nC
td(on)	Turn-on Delay Time	VDD=10V, ID=2A, VGS=4.5V, RG=3Ω	--	3	--	nS
tr	Turn-on Rise Time		--	11	--	nS
td(off)	Turn-Off Delay Time		--	20	--	nS
tf	Turn-Off Fall Time		--	8	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	Tj=25°C, Is=2.5A	--	--	1.2	V

Typical Operating Characteristics



SOT-523 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°